

Item	Symbol	Ratings	Unit V 0250 V	
Collector to base voltage	V _{CBO}	30		
Collector to emitter voltage	V _{ceo}	20		
Emitter to base voltage	V _{EBO}	4	V	
Collector current	I _c	20	mA	
Collector power dissipation	Pc	100	mW	
Junction temperature	Tj	150	°C	
Storage temperature	Tstg	-55 to +150	°C	

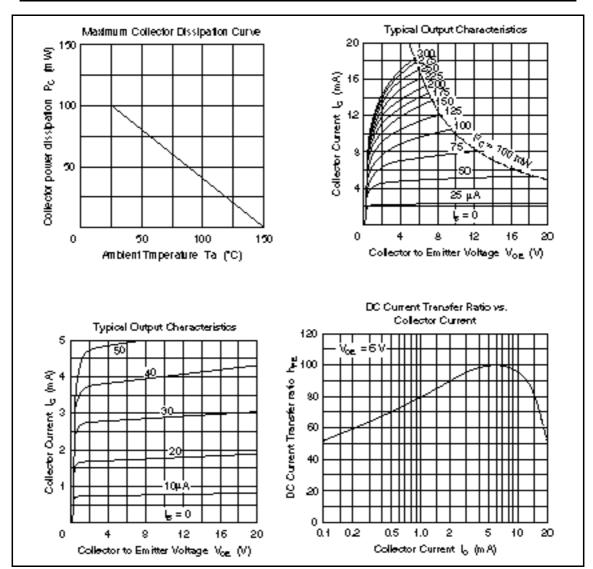


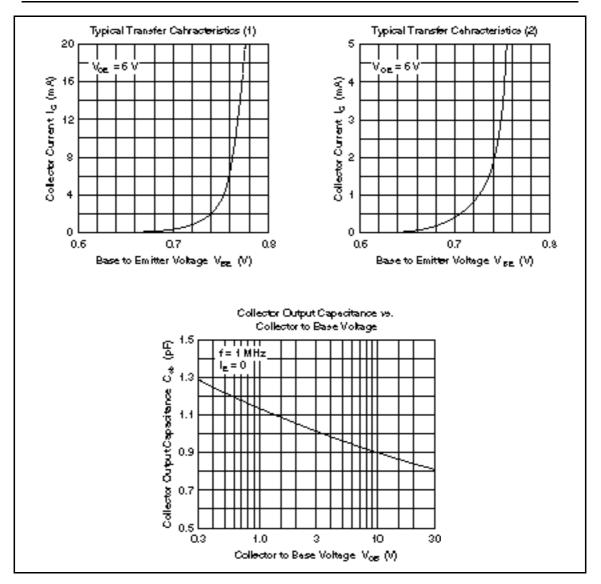
Electrical Characteristics (Ta = 25° C)

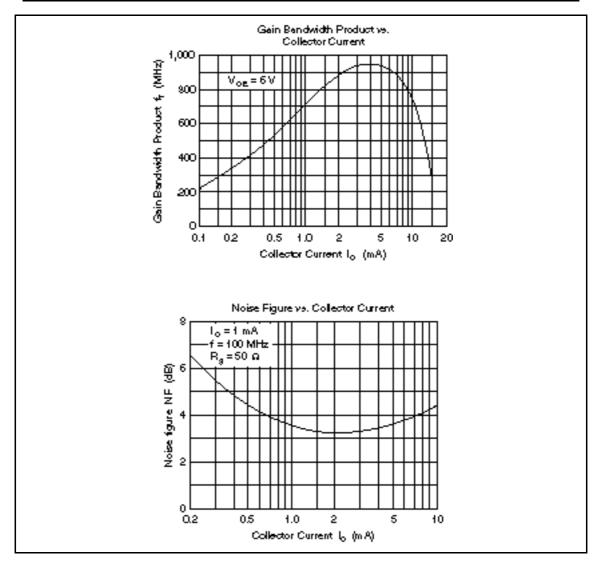
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{\rm (BR)CBO}$	30	—	—	V	$I_{c} = 10 \ \mu A, \ I_{E} = 0$
Collector to emitter breakdown voltage	$V_{(\text{BR})\text{CEO}}$	20	_	_	V	$I_c = 1 \text{ mA}, \text{ R}_{\text{BE}} =$
Emitter to base breakdown voltage	$V_{(\text{BR})\text{EBO}}$	4	_	_	V	$I_{\rm E} = 10 \ \mu A, \ I_{\rm C} = 0$
Collector cutoff current	I _{CBO}		_	0.5	μA	$V_{CB} = 10 \text{ V}, I_{E} = 0$
DC current transfer ratio	h_{FE}^{*1}	60	_	200		V_{ce} = 6 V, I_c = 1 mA
Base to emitter voltage	V_{BE}		0.72	_	V	V_{ce} = 6 V, I_c = 1 mA
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	_	0.17	_	V	$I_c = 20$ mA, $I_B = 4$ mA
Gain bandwidth product	f_{τ}	450	940	—	MHz	V_{ce} = 6 V, I_c = 5 mA
Collector output capacitance	Cob		0.9	1.2	pF	$V_{_{CB}} = 10 \text{ V}, \text{ I}_{_{E}} = 0, \text{ f} = 1 \text{ MHz}$
Power gain	PG	17	20	_	dB	V_{ce} = 6 V, I _c = 1 mA, f = 100 MHz
Noise figure	NF	_	3.5	5.5	dB	$V_{ce} = 6 V, I_c = 1 mA,$ f = 100 MHz, R _g = 50
Input admittance (typ)	yie	1.3 + j5.3			mS	V_{ce} = 6 V, I_c = 1 mA, f = 100 MHz
Reverse transfer admittance (typ)	yre	-0.078 - j0.41			mS	_
Foward transfer admittance (typ)	yfe	32 – j10			mS	_
Output admittance (typ)	yoe	0.08 + j0.82			mS	_

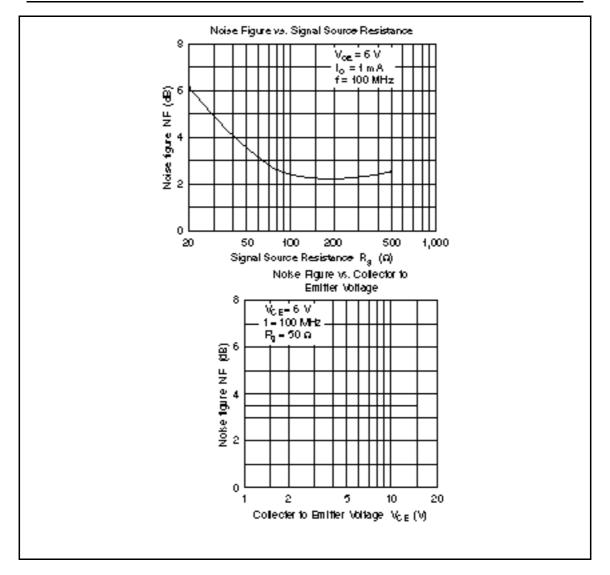
B C

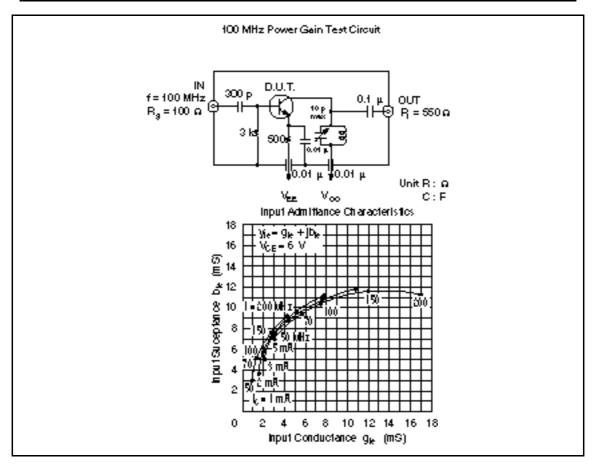
60 to 120 100 to 200

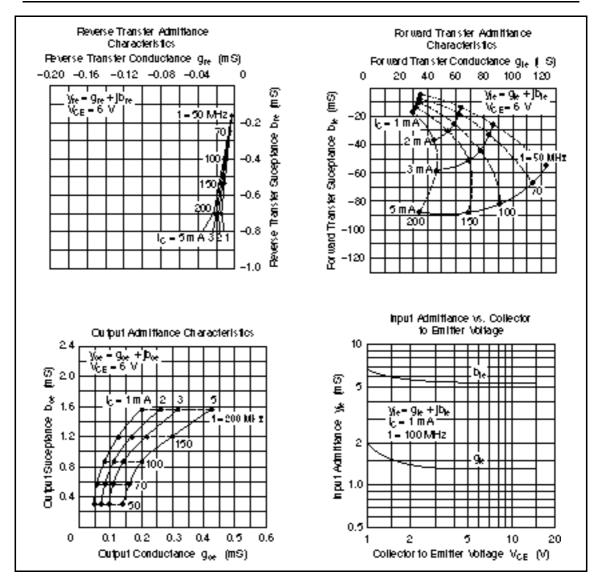


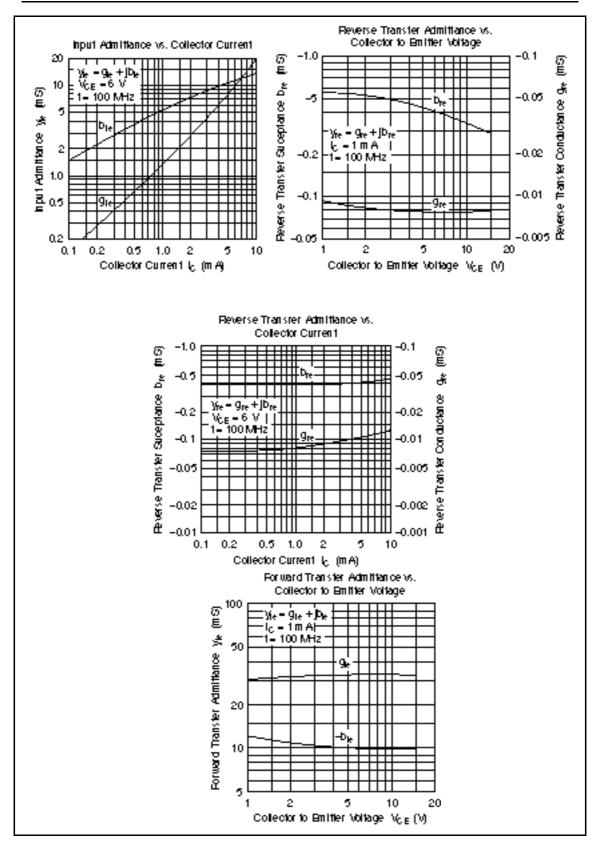


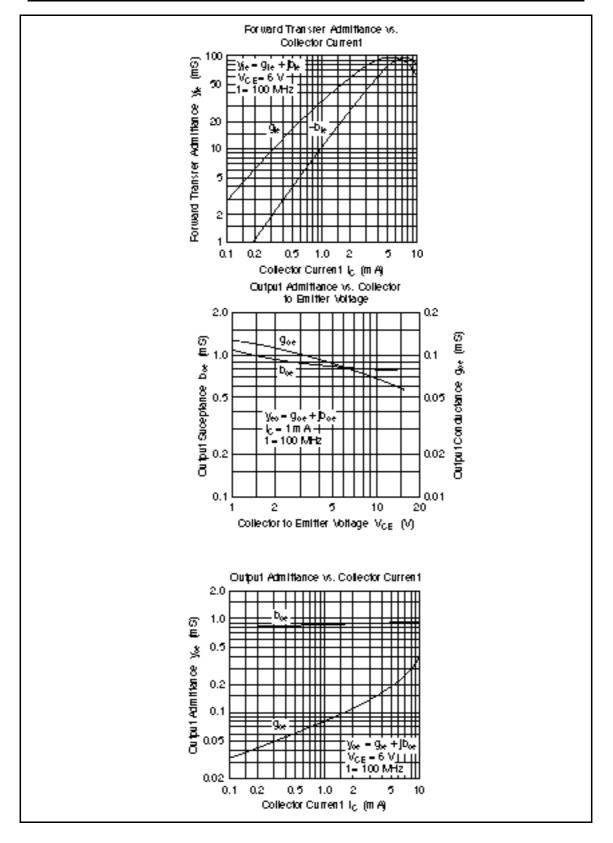












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